



# InGaN-based UV photodiode

Model: GT-UVV-L

## General Features:

- Indium Gallium Nitride Based Material
- Photovoltaic mode operation
- TO-46 metal housing
- High responsivity and low dark current

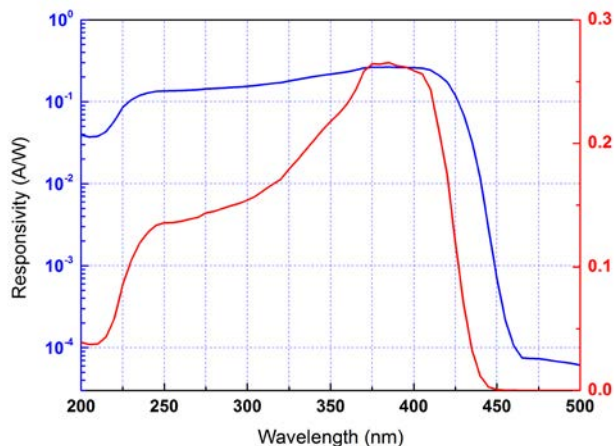


**Applications:** UV LED Monitoring, UV radiation dose measurement, UV Curing

## Specifications:

Parameters	Symbol	Value	Unit
<b>Maximum ratings</b>			
Operation temperature range	$T_{opt}$	-25-85	°C
Storage temperature range	$T_{sto}$	-40-85	°C
Soldering temperature (3 s)	$T_{sol}$	260	°C
Reverse voltage	$V_{r-max}$	-10	V
<b>General characteristics (25 °C)</b>			
Chip size	A	1	mm <sup>2</sup>
Dark current ( $V_r = -5$ V)	$I_d$	<1	nA
Temperature coefficient	$T_c$	0.05	%/°C
Capacitance (at 0 V and 1 MHz)	$C_p$	60	pF
<b>Spectral response characteristics (25 °C)</b>			
Wavelength of peak responsivity	$\lambda_p$	385	nm
Peak responsivity (at 385 nm)	$R_{max}$	0.267	A/W
Spectral response range ( $R=0.1 \times R_{max}$ )	-	200-440	nm
UV-visible rejection ratio ( $R_{max}/R_{400\text{ nm}}$ )	-	$>10^4$	-

## Spectral response



## Package dimensions

